

Silicon Power Schottky Diode

$V_{RRM} = 20 \text{ V - } 100 \text{ V}$

$I_F = 200 \text{ A}$

Features

- High Surge Capability
- Types up to 100 V V_{RRM}
- Isolation Type Package

Three Tower Package

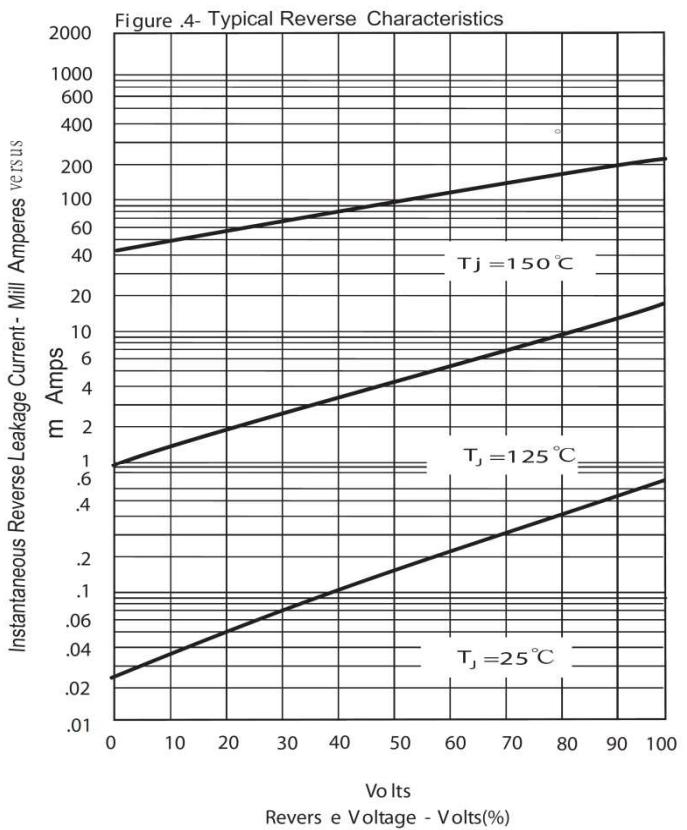
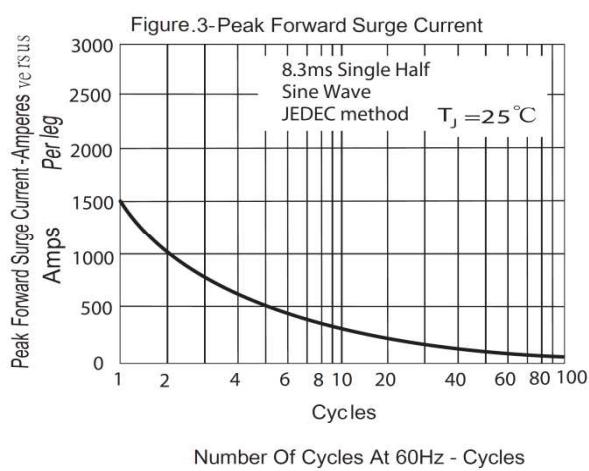
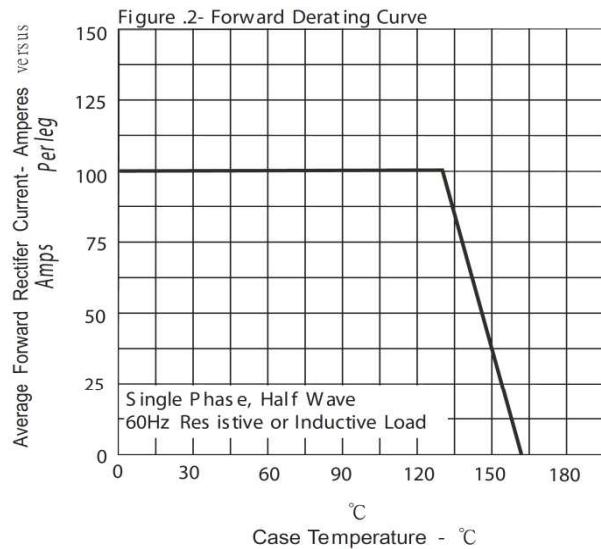
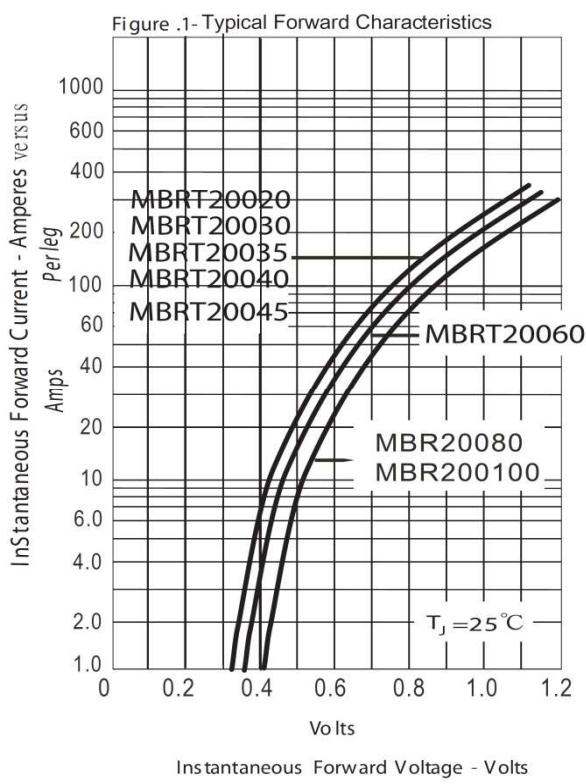


Maximum ratings, at $T_j = 25 \text{ }^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBRT20020 (R)	MBRT20030 (R)	MBRT20035 (R)	MBRT20040 (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		20	30	35	40	V
RMS reverse voltage	V_{RMS}		14	21	25	28	V
DC blocking voltage	V_{DC}		20	30	35	40	V
Continuous forward current	I_F	$T_C \leq 125 \text{ }^\circ\text{C}$	200	200	200	200	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25 \text{ }^\circ\text{C}, t_p = 8.3 \text{ ms}$	1500	1500	1500	1500	A
Operating temperature	T_j		-40 to 150	-40 to 150	-40 to 150	-40 to 150	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to 175	-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$

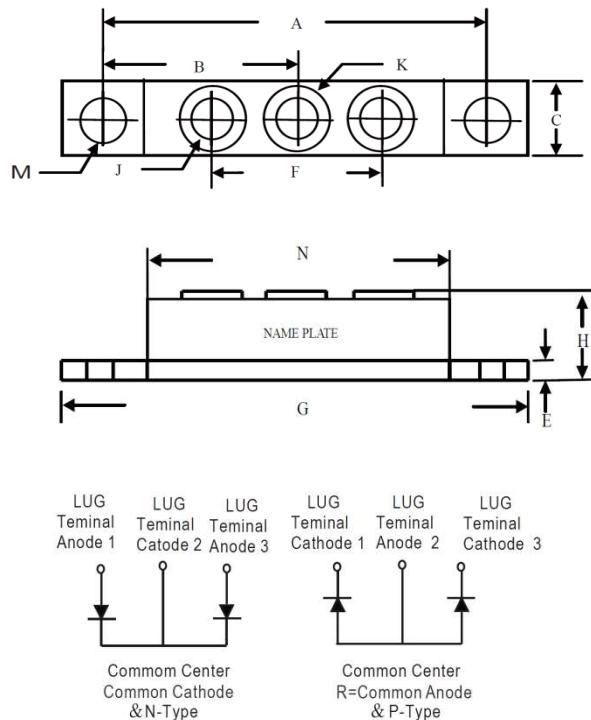
Electrical characteristics, at $T_j = 25 \text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	MBRT20020 (R)	MBRT20030(R)	MBRT20035 (R)	MBRT20040 (R)	Unit
Diode forward voltage	V_F	$I_F = 100 \text{ A}, T_j = 25 \text{ }^\circ\text{C}$	0.75	0.75	0.75	0.75	V
Reverse current	I_R	$V_R = 20 \text{ V}, T_j = 25 \text{ }^\circ\text{C}$ $V_R = 20 \text{ V}, T_j = 125 \text{ }^\circ\text{C}$	1	1	1	1	mA
Thermal characteristics							
Thermal resistance, junction - case	R_{thJC}		0.18	0.18	0.18	0.18	$^\circ\text{C/W}$



Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



DIM	Inches		Millimeters	
	Min	Max	Min	Max
A	3.150	NOM	80.01	NOM
B	1.565	1.585	39.75	40.26
C	.700	.800	17.78	20.32
E	.119	.132	3.02	3.35
F	1.327	REF	33.72	REF
G	3.55	3.65	90.17	92.71
H	----	.73	----	18.30
J	1/4-20 UNC FULL			
K	.472	.511	12	13
M	.275	.295	6.99	7.49
N	2.38	2.46	60.5	62.5